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Substitute for form 1449A/B/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)		Complete If Known			
		Application Number	10/602,716-Conf. #9955		
		Filing Date	June 25, 2003		
		First Named Inventor	Chandra Mouli		
		Art Unit	2811		
		Examiner Name	D. Kang Colleen Matthews		
Sheet	1	of	1	Attorney Docket Number	M4065.0904/P904

U.S. PATENT DOCUMENTS					
Examiner Initials [*]	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code ² (if known)			
CAM	AA	2002/0190287	12/19/2002	Mann et al.	

FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No. ¹	Foreign Patent Document	Publication Date	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	Y ⁶
		Country Code ³ -Number ⁴ -Kind Code ⁵ (if known)	MM-DD-YYYY			
CAM	BA	EP 0 798 785	10/01/1997			
CAM	BB	JP 01-232765	09/18/1989			X

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 809. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. ¹ Applicant's unique citation designation number (optional). ² See Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 801.04. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

NON PATENT LITERATURE DOCUMENTS					
Examiner Initials [*]	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.			Y ⁶
CAM	CA	Kim, K.T. et al. – "Tungsten Silicide/Titanium Nitride Compound Gate," June 4, 1990, Symposium on VLSI Technology, Honolulu, June 4-7, 1990, New York, IEEE, US, pgs 115-116.			
CAM	CB	Long, Wei et al. – "Dual-Material Gate (DMG) Field Effect Transistor," May 1999, IEEE Transactions on Electron Devices, IEEE Inc. New York, US, pgs. 865-870.			
CAM	CC	Ponomarev, Y.V. et al. – "Gate-Workfunction Engineering Using Poly-(Si,Ge) for High-Performance 0.18 μ m CMOS Technology," International Electron Devices Meeting 1997, IEDM Technical Digest, Washington, DC, Dec. 7-10, 1997, New York, NY, IEEE, US, 12/7/1997, pgs. 829-832.			
CAM	CD	Yagishita, Atsushi et al. – "Dynamic Threshold Voltage Damascene Metal Gate MOSFET (DT-DMG-MOS) Technology for Very Low Voltage Operation of Under 0.7 V," IEEE Transactions on Electron Devices, IEEE Inc. New York, US, vol. 49, no. 3, March 2002, pgs. 422-428.			
CAM	CE	International Search Report dated 11/30/2004.			

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 809. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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Examiner Signature	Colleen Matthews	Date Considered	12/30/2007
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